

IN THE CLAIMS:

Claim 1 (currently amended): A semiconductor light emitting device comprising at least one semiconductor light emitting element of edge-emission type, a first heat sink and a second heat sink,

wherein at least a part of an electrode for a first-conduction-type semiconductor of the semiconductor light emitting element is in thermally ~~preferable~~ joining contact with the first heat sink;

at least a part of an electrode for a second-conduction-type semiconductor of the semiconductor light emitting element is in thermally ~~preferable~~ joining contact with the second heat sink; and

the first heat sink and the second heat sink are either in thermally ~~preferable~~ joining direct contact ~~with each other or in thermally joining contact with interposition of an adhesive~~ in a junction overlooking one of the two side planes which do not compose facets of a cavity in the semiconductor light emitting element.

Claim 2 (original): The semiconductor light emitting device as claimed in Claim 1, wherein a portion of the electrode for the first-conduction-type semiconductor of the semiconductor light emitting element is not in contact with the first heat sink in the vicinity of the front facet of the element; and

a portion of the electrode for the second-conduction-type semiconductor of the semiconductor light emitting element is in contact with the second heat sink in the vicinity of the

front facet of the element.

Claim 3 (original): The semiconductor light emitting device as claimed in Claim 1, wherein the surface of the first heat sink which is kept in contact with the semiconductor light emitting element has an effective electro-conductivity with at least one surface which is not kept in contact with the semiconductor light emitting element.

Claim 4 (original): The semiconductor light emitting device as claimed in Claim 1, wherein a surface of the second heat sink which is kept in contact with the semiconductor light emitting element has no electro-conductivity with any surface which is not kept in contact with the semiconductor light emitting element.

Claim 5 (original): The semiconductor light emitting device as claimed in Claim 1, wherein the diameter of a lead wire for introducing electric current to the semiconductor light emitting element and which is kept in contact with at least one of the group consisting of semiconductor light emitting element, the first heat sink and the second heat sink is 35 μm or less; and

a pair of portions not connected directly with each other are connected with each other with a plurality of lead wires.

Claim 6 (previously presented): The semiconductor light emitting device as claimed in

Claim 1, wherein a groove is provided in the vicinity of the junction of the first heat sink and the second heat sink, into which an adhesive is provided on a protrusion part of the second heat sink to join the first heat sink and the second heat sink: wherein the groove prevent an excessive adhesive from reaching the semiconductor light emitting element.

Claim 7 (original): The semiconductor light emitting device as claimed in Claim 1, wherein at least a part of the electrode for the first-conduction-type semiconductor is in contact with the first heat sink, interposed with a first adhesive; at least a part of the first heat sink is in contact with the second heat sink, interposed with a second adhesive; and the total weight of the second adhesive is twice or more heavier than the total weight of the first adhesive.

Claim 8 (original): The semiconductor light emitting device as claimed in Claim 7, wherein the total weight of the second adhesive is five times or more heavier than the total weight of the first adhesive.

Claim 9 (original): The semiconductor light emitting device as claimed in Claim 1, wherein at least one of the electrodes of the semiconductor light emitting element has an Au layer having a thickness of 30 to 100 μm .

Claim 10 (original): The semiconductor light emitting device as claimed in Claim 1, wherein the first conduction type is p-type, and the second conduction type is n-type.

Claim 11 (original): The semiconductor light emitting device as claimed in Claim 1, wherein the semiconductor light emitting element is a semiconductor laser diode, and the front facet thereof is connected to an optical fiber so as to compose a semiconductor laser module.

Claim 12 (original): The semiconductor light emitting device as claimed in Claim 11, wherein the tip of the optical fiber has a light condensation focusing function, and is processed so as to be optically coupled directly with the front facet of the semiconductor laser diode.

Claim 13 (new): The semiconductor light emitting device as claimed in Claim 1, wherein the adhesive is a solder material.

Claim 14 (New): The semiconductor light emitting device as claimed in Claim 1, wherein the solder material contains AuGe, AuSn, AgSn, PbSn, InSn, SnBi or In.

Claim 15 (New): The semiconductor light emitting device as claimed in Claim 1, wherein at least a part of an electrode for the first-conduction-type semiconductor of the semiconductor light emitting element and the first heat sink are either in thermally joining direct contact or in thermally joining contact with interposition of an adhesive.

Claim 16 (New): The semiconductor light emitting device as claimed in Claim 1, wherein at least a part of an electrode for the second-conduction-type semiconductor of the semiconductor light emitting element and the second heat sink are either in thermally joining direct contact or in thermally joining contact with interposition of an adhesive.